

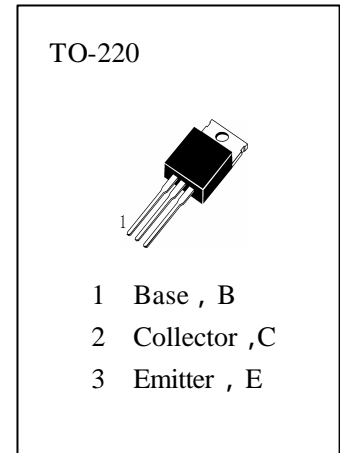


APPLICATIONS

high Voltage power switch switching Application.

ABSOLUTE MAXIMUM RATINGS ($T_a=25$)

T_{stg}	Storage Temperature.....	-65~150
T_j	Junction Temperature.....	150
P_C	Collector Dissipation($T_c=25$).....	70W
V_{CBO}	Collector-Base Voltage.....	800V
V_{CEO}	Collector-Emitter Voltage.....	400V
V_{EBO}	Emitter-Base Voltage.....	7V
I_C	Collector Current (DC)	5A
I_{CP}	Collector Current(Pulse).....	10A
I_b	Base Current.....	3A



ELECTRICAL CHARACTERISTICS ($T_a=25$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	800			V	$I_C=1mA, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	400			V	$I_C=5mA, I_B=0$
BV_{EBO}	Emitter-Base Breakdown Voltage	7			V	$I_E=1mA, I_C=0$
I_{CBO}	Collector Cut-off Current			10	μA	$V_{CB}=500V, I_E=0$
I_{EBO}	Emitter Cut-off Current			10	μA	$V_{EB}=7V, I_C=0$
H_{FE}	*DC Current Gain	10				$V_{CE}=5V, I_C=0.3A$
$V_{CE(sat)}$	*Collector- Emitter Saturation Voltage			1.5	V	$I_C=2.5A, I_B=0.5A$
$V_{BE(sat)}$	*Base-Emitter Saturation Voltage			2.0	V	$I_C=2.5A, I_B=0.5A$
f_T	Current Gain-Bandwidth Product		10		MHz	$V_{CE}=5V, I_C=0.1A$
C_{ob}	Output Capacitance			40	pF	$V_{CB}=10V, f=1MHz$
t_{ON}	Turn On Time			1	μS	} $V_{CC}=150V, I_C=2.5A,$ $I_{b1}=-I_{b2}=0.5A, R_L=60$
t_{STG}	Storage Time			3	μS	
t_F	Fall Time			0.8	μS	

*Pulse Test : PW 300 μs , Duty cycle 2% Pulse

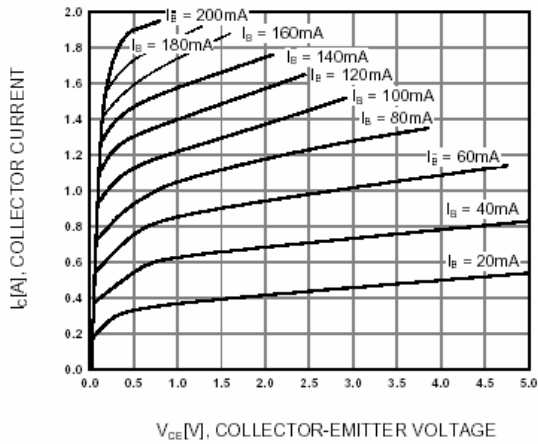


Figure 1. Static Characteristic

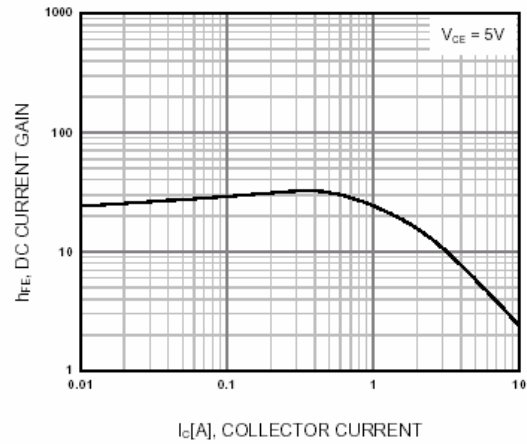


Figure 2. DC current Gain

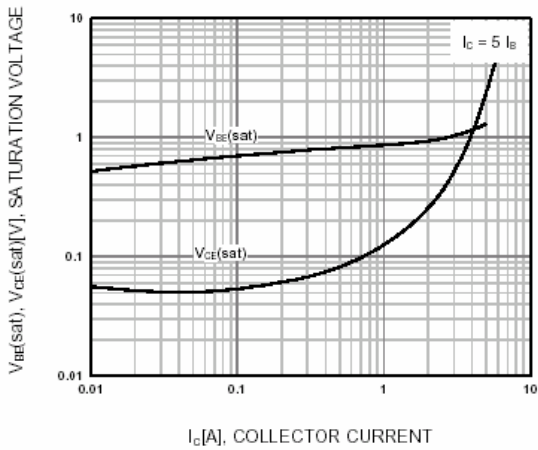


Figure 3. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

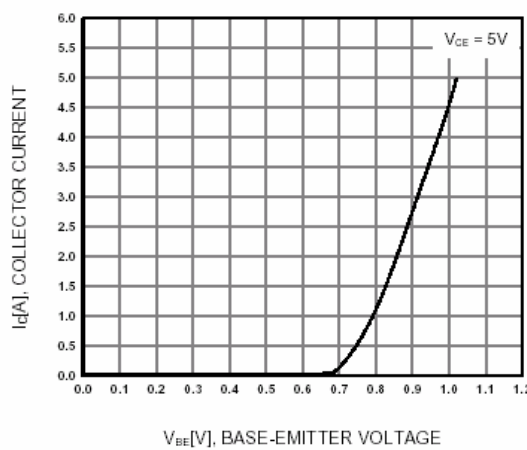


Figure 4. Base-Emitter On Voltage

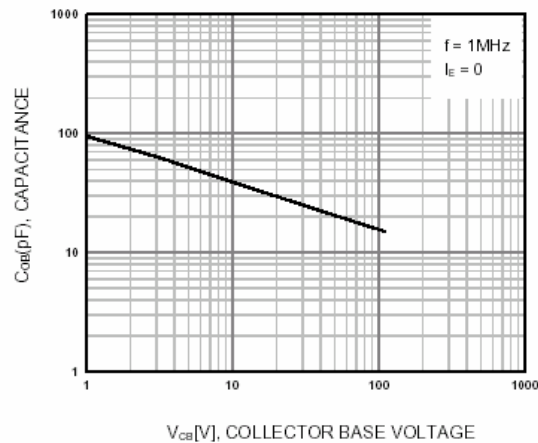


Figure 5. Collector Output Capacitance

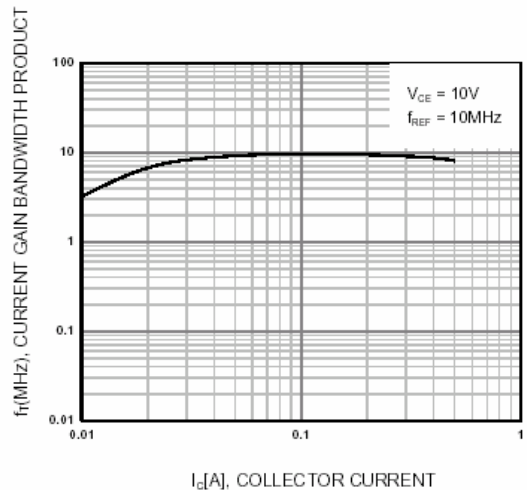


Figure 6. Current Gain Bandwidth Product

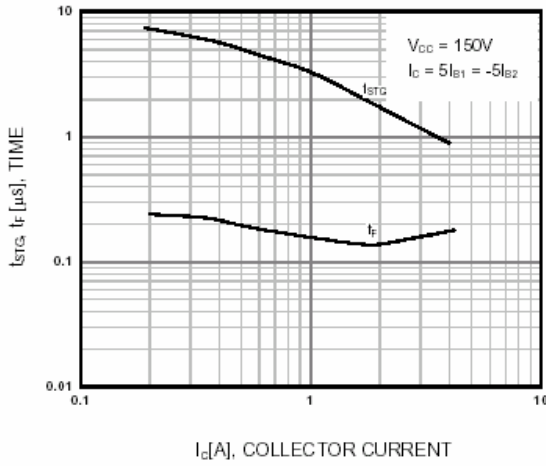


Figure 7. Switching Time

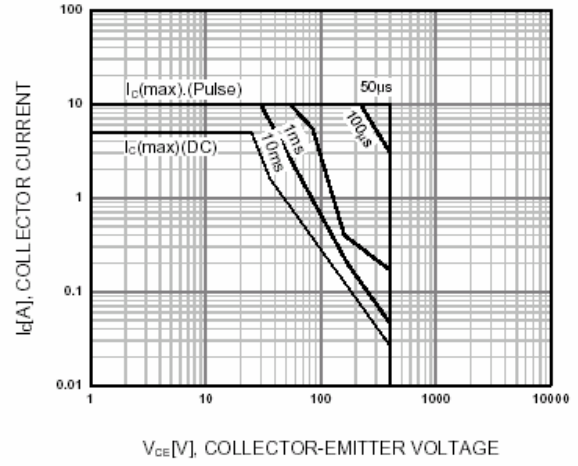


Figure 8. Safe Operating Area

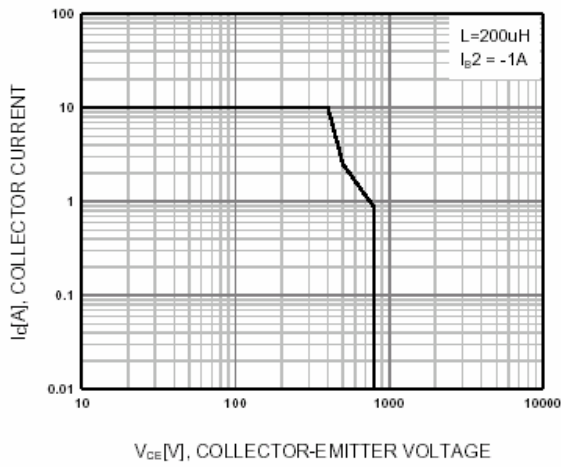


Figure 9. Reverse Bias Safe Operating Area

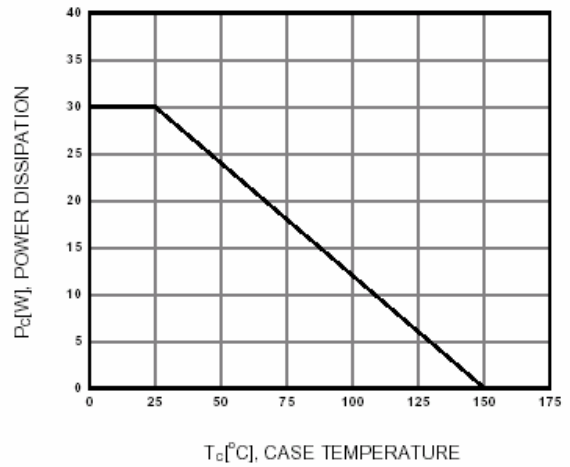


Figure 10. Power Derating